Daisuke Tahara

List of Publications by Year
in descending order

11	292	1163117 8	1372567 10
papers	citations	h-index	g-index

11	11	11	277
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Epitaxial growth of Î±-Ga2O3 thin films on a-, m-, and r-plane sapphire substrates by mist chemical vapor deposition using Î±-Fe2O3 buffer layers. Materials Letters, 2017, 205, 28-31.	2.6	63
2	Microstructures and rotational domains in orthorhombic Îµ-Ga₂O₃ thin films. Japanese Journal of Applied Physics, 2018, 57, 115601.	1.5	61
3	Heteroepitaxial growth of Îµ-(AlxGa1â^'x)2O3 alloy films on c-plane AlN templates by mist chemical vapor deposition. Applied Physics Letters, 2018, 112, .	3.3	59
4	Use of mist chemical vapor deposition to impart ferroelectric properties to Îµ-Ga2O3 thin films on SnO2/c-sapphire substrates. Materials Letters, 2018, 232, 47-50.	2.6	26
5	Single-Domain and Atomically Flat Surface of Îº-Ga₂O₃ Thin Films on FZ-Grown Îµ-GaFeO₃ Substrates via Step-Flow Growth Mode. ACS Omega, 2020, 5, 29585-29592.	3.5	24
6	Phase control of Î±- and Îº-Ga2O3 epitaxial growth on LiNbO3 and LiTaO3 substrates using Î±-Fe2O3 buffer layers. AIP Advances, 2020, 10, .	1.3	18
7	van der Waals epitaxy of ferroelectric Îµ-gallium oxide thin film on flexible synthetic mica. Japanese Journal of Applied Physics, 2020, 59, 025503.	1.5	15
8	Epitaxial growth of Î³-(AlxGa1-x)2O3 alloy thin films on spinel substrates via mist chemical vapor deposition. Journal of Alloys and Compounds, 2021, 851, 156927.	5.5	14
9	Heteroepitaxial growth of Îµ-Ga<inf>2</inf>O<inf>3</inf> thin films on cubic (111) GGG substrates by mist chemical vapor deposition. , 2017, , .		5
10	A preliminary study on mist CVD-derived ferroelectric Hf_{1â^'x}Zr _x O₂ films featuring its possibility of suitable operation for non-volatile analog memory. Japanese Journal of Applied Physics, 2020, 59, SPPB09.	1.5	5
11	Mist chemical vapor deposition study of 20 and 100 nm thick undoped ferroelectric hafnium oxide films on n+-Si(100) substrates. Japanese Journal of Applied Physics, 2019, 58, SLLB10.	1.5	2